

C Thomidis

List of Publications by Year in descending order

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14
papers

262
citations

840585

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14
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14
docs citations

14
times ranked

404
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth and properties of near-UV light emitting diodes based on InN/GaN quantum wells. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1070-1073.	0.8	57
2	Growth of In nitride quantum dots and their applications to blue-green LEDs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2560-2565.	0.8	28
3	Ultraviolet electroabsorption modulator based on AlGaIn-GaN multiple quantum wells. Journal of Applied Physics, 2005, 97, 123515.	1.1	22
4	Enhanced internal quantum efficiency and light extraction efficiency from textured GaIn-AlGaIn quantum wells grown by molecular beam epitaxy. Journal of Applied Physics, 2006, 99, 064904.	1.1	22
5	Molecular beam epitaxy growth of AlGaIn quantum wells on 6H-SiC substrates with high internal quantum efficiency. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 02B119.	0.6	22
6	High power ultraviolet light emitting diodes based on GaIn-AlGaIn quantum wells produced by molecular beam epitaxy. Journal of Applied Physics, 2006, 100, 104506.	1.1	21
7	Investigation of excitons in AlGaIn/GaN multiple quantum wells by lateral photocurrent and photoluminescence spectroscopies. Journal of Applied Physics, 2004, 95, 3495-3502.	1.1	20
8	Growth and silicon doping of AlGaIn films in the entire alloy composition by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2220-2223.	0.8	18
9	Growth of InN films by RF plasma-assisted MBE and cluster beam epitaxy. Journal of Crystal Growth, 2006, 288, 254-260.	0.7	15
10	Well width dependence of disorder effects on the optical properties of AlGaIn-GaN quantum wells. Applied Physics Letters, 2004, 85, 3068-3070.	1.5	13
11	Strong Diffusion Suppression of Low Energy-Implanted Phosphorous in Germanium by N ₂ Co-Implantation. ECS Solid State Letters, 2015, 4, P47-P50.	1.4	11
12	InGaIn-based LEDs grown by plasma-assisted MBE on (0001) sapphire with GaN QDs in the nucleation layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2309-2311.	0.8	7
13	Phosphorous Diffusion in N ₂ -Implanted Germanium during Flash Lamp Annealing: Influence of Nitrogen on Ge Substrate Damage and Capping Layer Engineering. ECS Journal of Solid State Science and Technology, 2017, 6, P418-P428.	0.9	5
14	InGaIn-based LEDs grown by plasma-assisted MBE on (0001) sapphire with GaN QDs in the nucleation layer. , 2008, 5, 2309.		1